

Supplementary Information

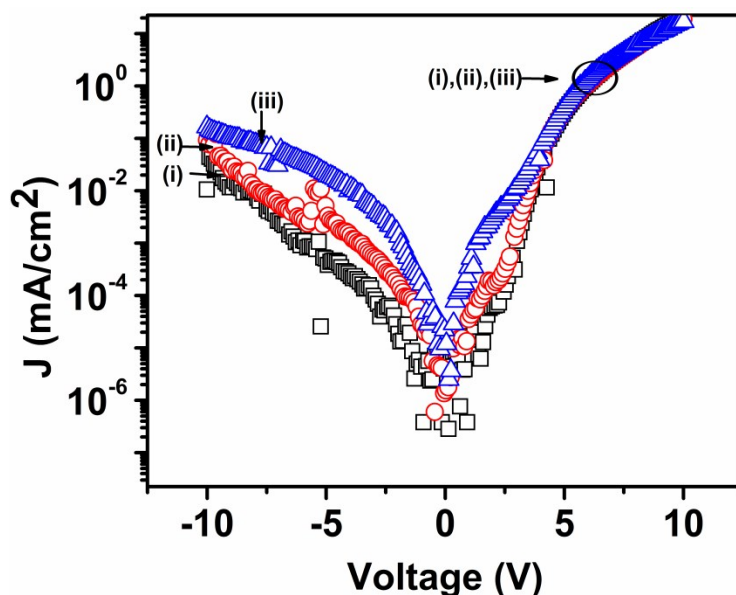


Fig. S1 Current density-voltage characteristics of devices i, ii and iii

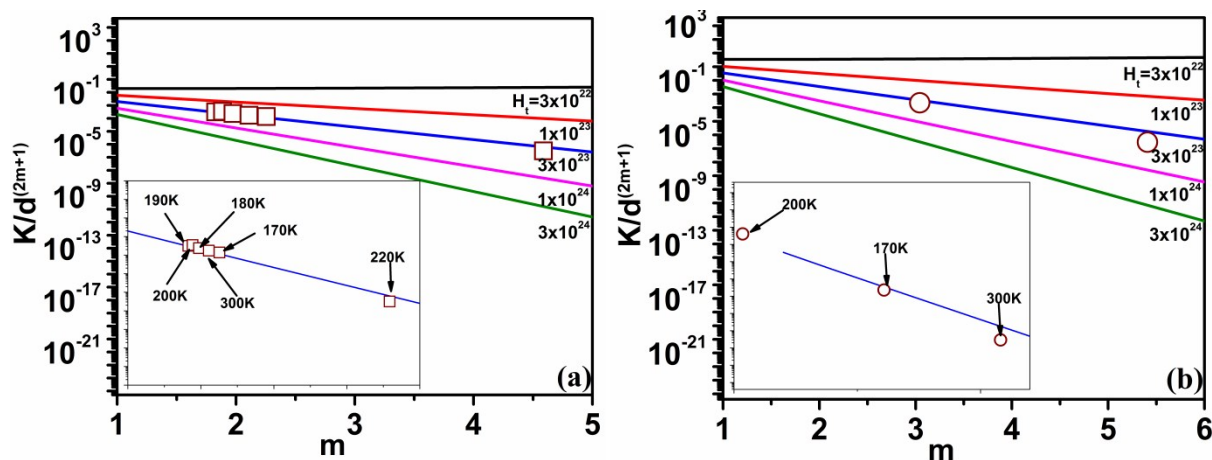


Fig. S2 Variation of $K/d^{(2m+1)}$ with m to find the trap density in Alq_3 device at various temperatures (a) before annealing and (b) after annealing. The inset gives the different temperature values corresponding to the measured points (All quantities in SI units)

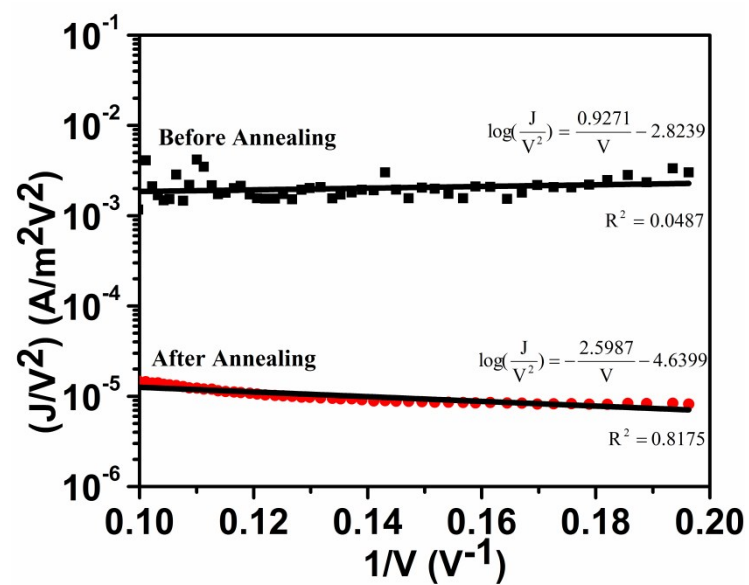


Fig.S3 Fit for tunneling injection in m-MTDATA single layer device before and after annealing.